

# RPC with Gallium Arsenide electrodes, a solution for medium sized high-rate detectors

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# DETECTOR DESCRIPTION

✓ High Rate RPC

$$V_{\text{gas}} = V_{\text{gen}} - \rho d \bar{Q} \phi$$

State of the art:  $\bar{Q} \sim 6 \text{ pC}$ ;  $Q_{\text{th}} \sim 2 - 4 \text{ fC}$ ;  $d = 1.25 \text{ mm}$ ;  $\rho \sim 10^{10} \Omega \text{ cm}$  ;

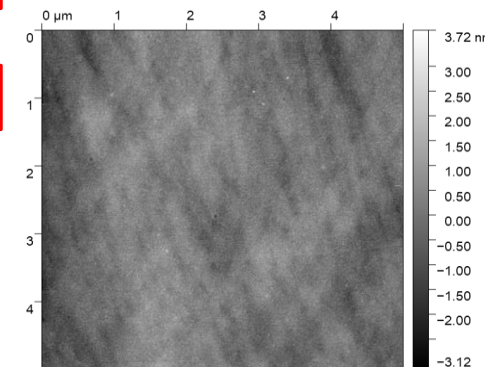
->  $\phi \sim 7 \text{ kHz/cm}^2$

$\phi \sim 1 \text{ MHz/cm}^2$  ←

The HPL electrodes guarantee stable operation up to a total integrated charge of  $0.3 \text{ C/cm}^2$  --> **Effective rate capability significantly limited by the experiment lifetime and background radiation**

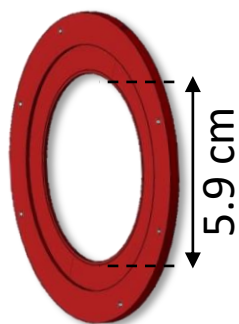
A new material immune to the ageing effect should improve the effective rate capability of a factor ten, just with  $10^{10} \Omega \text{ cm}$  resistivity

Material	Semi Insulating undoped GaAs
Thickness	640 – 643; $\mu\text{m}$
Diameter	3"
Resistivity	$1.4 \times 10^8 \Omega \text{ cm}$
Surface treatment	both polished
Growth method	VGF
Orientation	(100) $\pm 0.01^\circ$
Mobility	$5300 \text{ cm}^2/\text{Vs}$

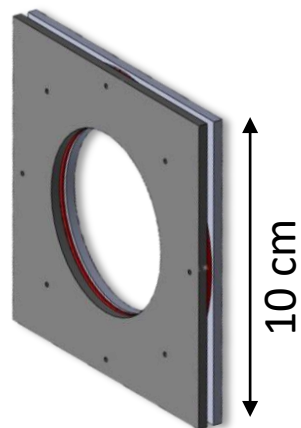


Thanks to Prof. M. Lucci for the GaAs metallization

Wafers spacer  
1 mm



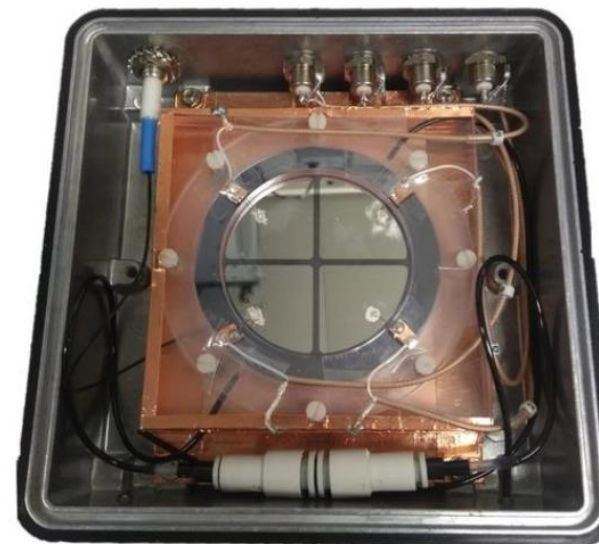
Wafers holder



Voltage supply	3–5 Volt
Sensitivity	2–4 mV/fC
Noise (independent from detector)	4000 e <sup>-</sup> RMS
Input impedance	100–50 Ohm
B.W.	10–100 MHz
Power consumption	10 mW/ch
Rise time $\delta(t)$ input	300–600 ps
Radiation hardness	1 Mrad, $10^{13} \text{ n cm}^{-2}$



Gas inlet  $\varnothing 2 \text{ mm} \rightarrow \varnothing 0.6 \text{ mm}$



Wafers sputtering holder

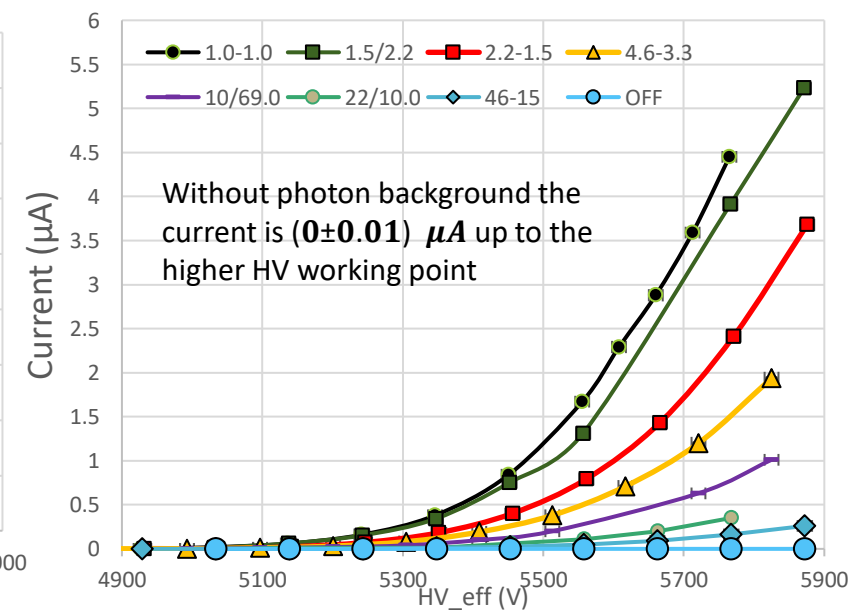
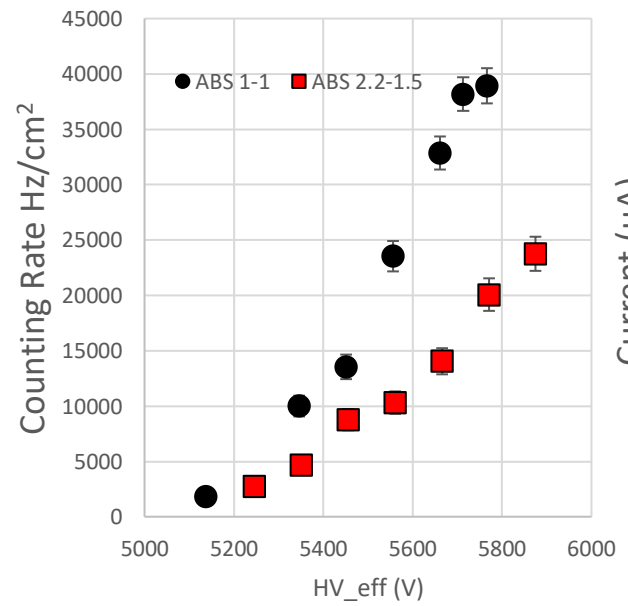
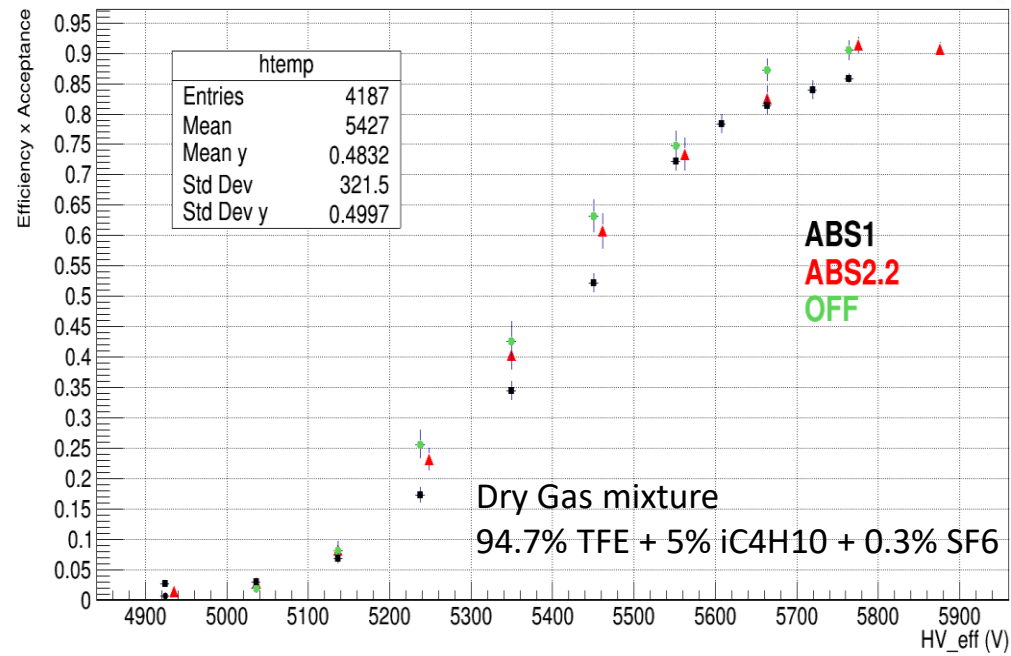
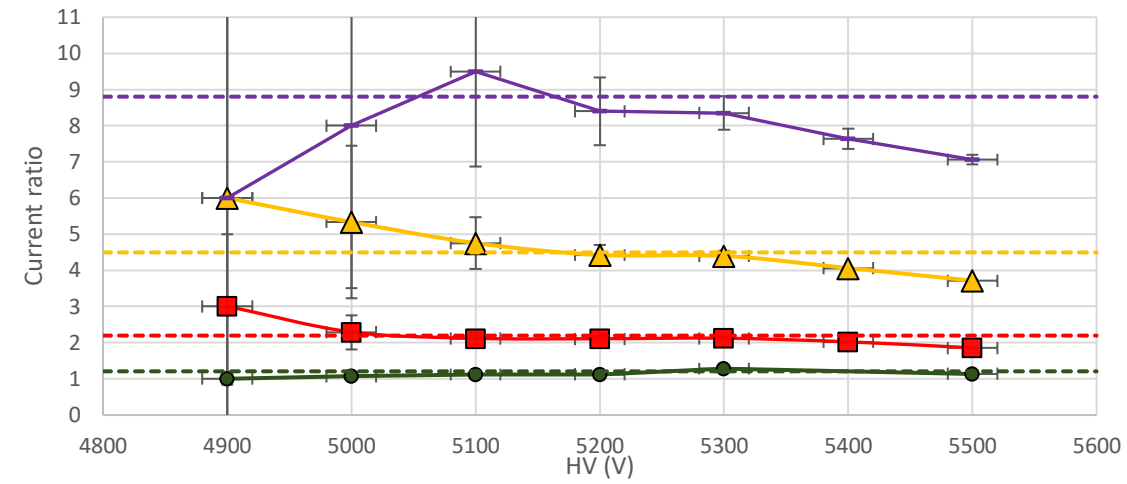
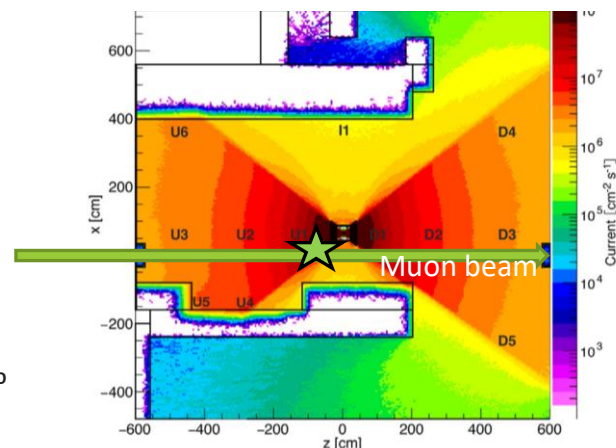


[R. Cardarelli et al, "Performance of RPCs and diamond detectors using a new very fast low noise preamplifier"]

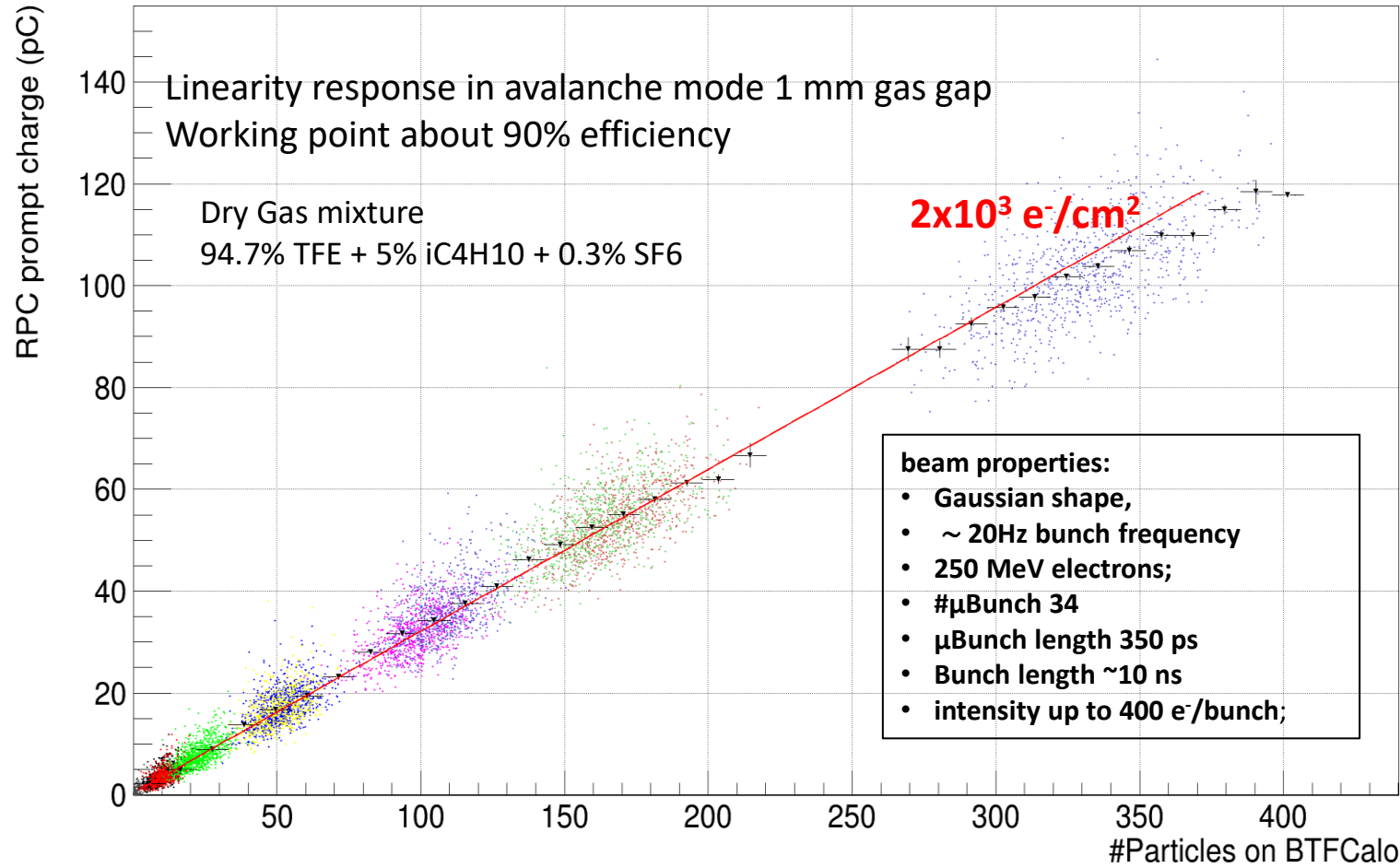
# HIGH-RATE TESTS

The rate capability was measured at GIF ++ at CERN. The detector efficiency response is constant up to the maximum observable flow at the Facility. The maximum counting rate measured is  $39 \text{ kHz/cm}^2$ , a value consistent with the photon current if we consider a photon conversion efficiency approximately 1-2%

The measured attenuation of the source is consistent with the reference values



# BUNCHED PARTICLES RESPONSE: LINEARITY AND TIME RESOLUTION



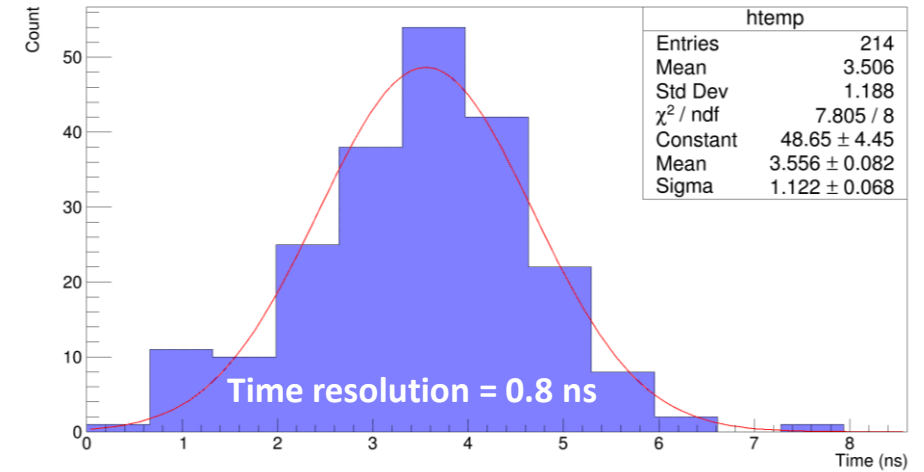
[B. Buonomo, G. Mazzitelli and P. Valente "Performance and Upgrade of the DAFNE Beam Test Facility (BTF)"]

[A. Rocchi et al "Linearity and rate capability measurements of RPC with semi-insulating crystalline electrodes operating in avalanche mode"]

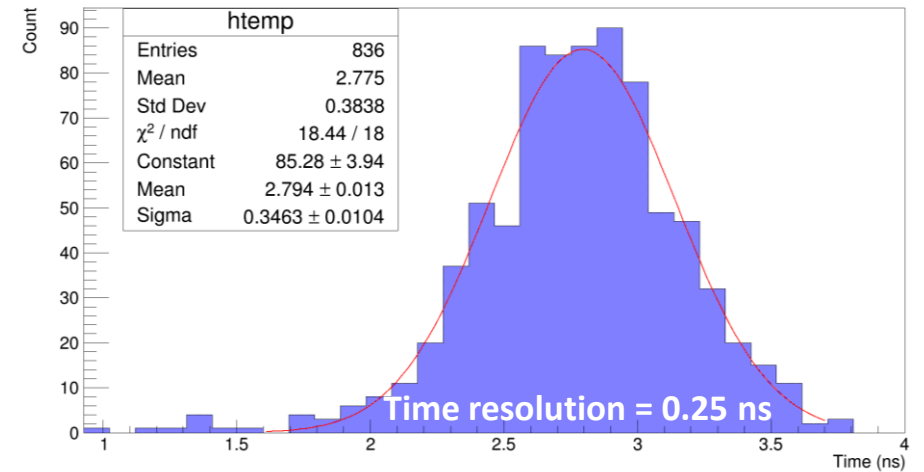
Time resolution with bunched particles improves as

$$\frac{1}{\sqrt{\text{synchronous particles}}}$$

1  $\text{e}^-/\text{bunch}$



$\sim 300 \text{ e}^-/\text{bunch}$  (10  $\text{e}^-/\mu\text{bunch}$ )



# Conclusions

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- The functionality of the detector has been extensively demonstrated: thanks to the **high sensitivity of the FE electronics** and to the **surface quality of the new GaAs wafers** the detector is stable up to full efficiency.
- The detector **performance is constant up to the maximum photon flux available at the GIF ++ facility**, and the maximum counting rate **measured is 39 kHz / cm<sup>2</sup> (about 1-2 ‰ photon efficiency)**.
- **Negligible random counting rate, negligible dark current**

## Open question:

- What changes in the physics of the detector when passing from an amorphous electrode to a semiconductive crystal?
- What role does electron mobility play?
- Does the resistivity of the electrode change with irradiation?
- What is the maximum rate capability of the detector?
- What is the aging damage of the detector?

## Costs

3-inch Undoped GaAs wafer about 100 \$/pz, 6-inch Undoped GaAs wafer about 200 \$/pz.

Electrode sputtering?